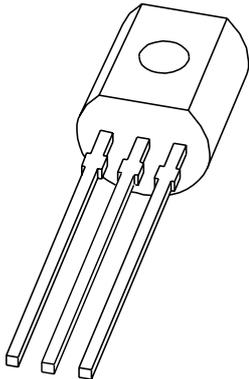


# DATA SHEET



**PBSS5350S**

**50 V low  $V_{CEsat}$  PNP transistor**

Product data sheet  
Supersedes data of 2001 Nov 19

2004 Aug 20

# 50 V low $V_{CEsat}$ PNP transistor

# PBSS5350S

### FEATURES

- High power dissipation (830 mW)
- Ultra low collector-emitter saturation voltage
- 3 A continuous current
- High current switching
- Improved device reliability due to reduced heat generation.

### APPLICATIONS

- Medium power switching and muting
- Linear regulators
- DC/DC convertor
- Supply line switching circuits
- Battery management applications
- Strobe flash units
- Heavy duty battery powered equipment (motor and lamp drivers).

### DESCRIPTION

PNP low  $V_{CEsat}$  transistor in a SOT54 plastic package.  
NPN complement: PBSS4350S.

### MARKING

TYPE NUMBER	MARKING CODE
PBSS5350S	S5350S

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	-50	V
$I_C$	collector current (DC)	-3	A
$I_{CM}$	peak collector current	-5	A
$R_{CEsat}$	equivalent on-resistance	<150	m $\Omega$

### PINNING

PIN	DESCRIPTION
1	base
2	collector
3	emitter

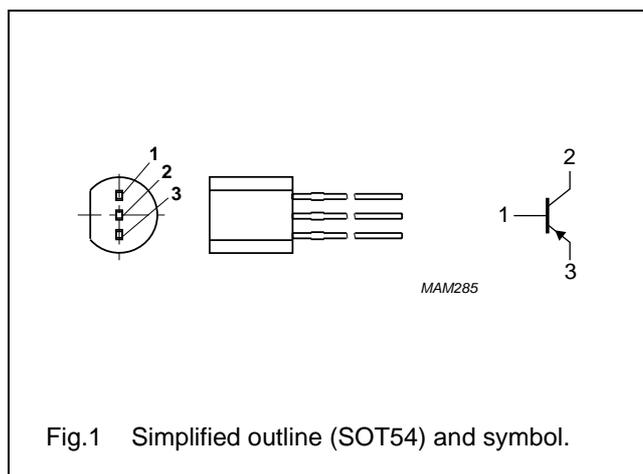


Fig.1 Simplified outline (SOT54) and symbol.

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	-	-60	V
$V_{CEO}$	collector-emitter voltage	open base	-	-50	V
$V_{EBO}$	emitter-base voltage	open collector	-	-6	V
$I_C$	collector current (DC)		-	-3	A
$I_{CM}$	peak collector current		-	-5	A
$I_{BM}$	peak base current		-	-1	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$ ; note 1	-	830	mW
$T_{stg}$	storage temperature		-65	+150	$^\circ\text{C}$
$T_j$	junction temperature		-	150	$^\circ\text{C}$
$T_{amb}$	operating ambient temperature		-65	+150	$^\circ\text{C}$

### Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.

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## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air; note 1	150	K/W

## Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.

## CHARACTERISTICS

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

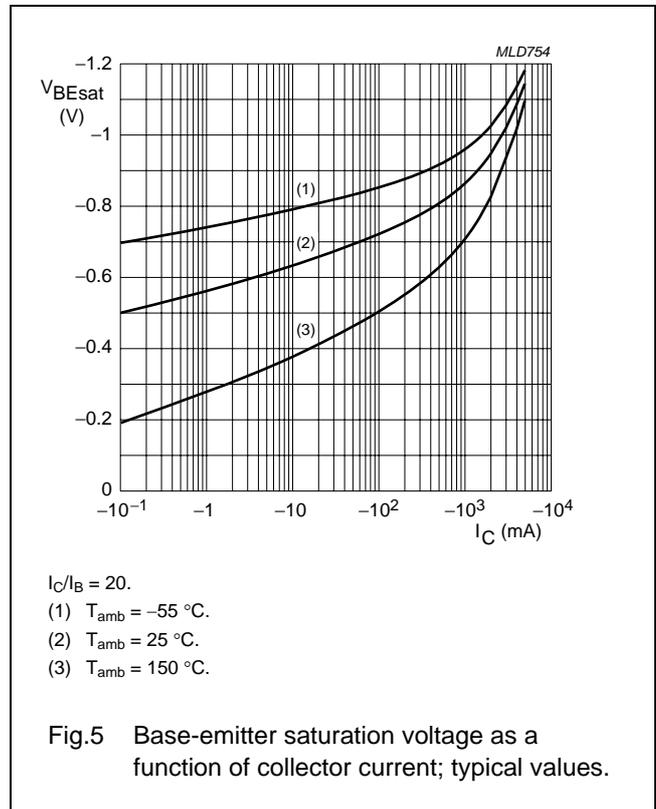
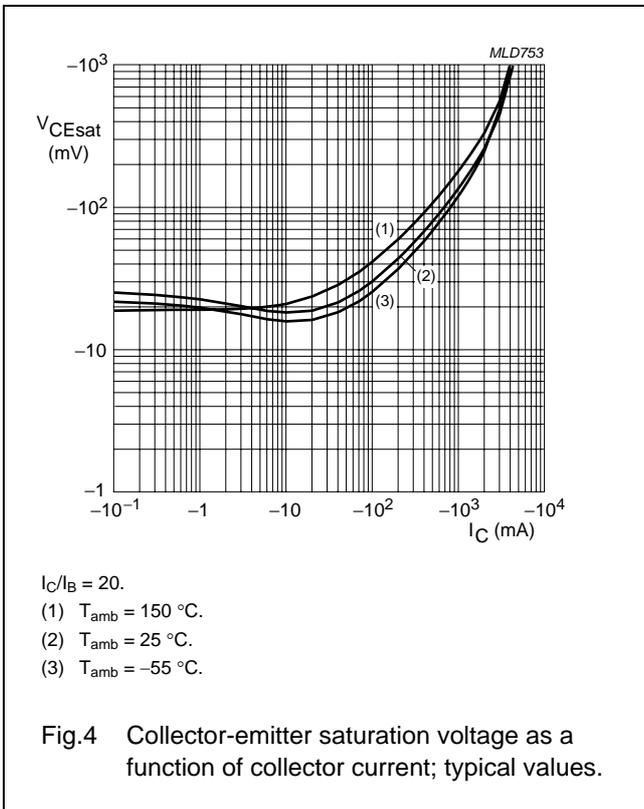
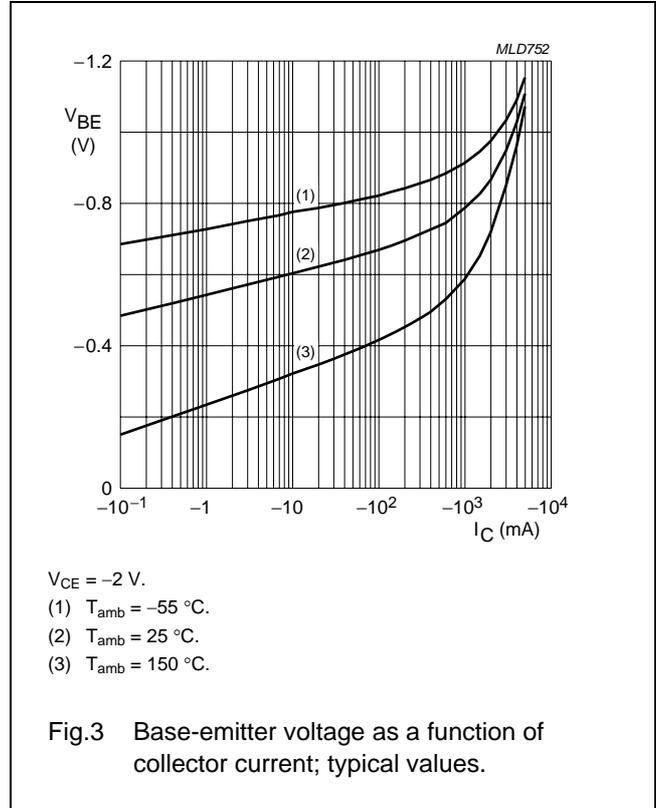
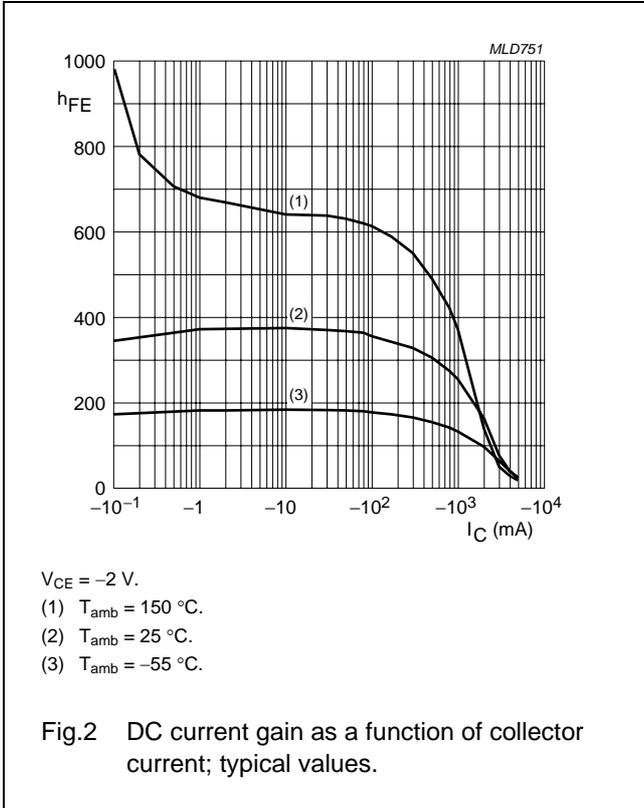
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector-base cut-off current	$V_{CB} = -50\text{ V}; I_E = 0$	–	–	–100	nA
		$V_{CB} = -50\text{ V}; I_E = 0; T_j = 150\text{ °C}$	–	–	–50	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0$	–	–	–100	nA
$h_{FE}$	DC current gain	$V_{CE} = -2\text{ V}; I_C = -500\text{ mA}$	200	–	–	
		$V_{CE} = -2\text{ V}; I_C = -1\text{ A}; \text{note 1}$	200	–	–	
		$V_{CE} = -2\text{ V}; I_C = -2\text{ A}; \text{note 1}$	100	–	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	–	–	–100	mV
		$I_C = -1\text{ A}; I_B = -50\text{ mA}$	–	–	–180	mV
		$I_C = -2\text{ A}; I_B = -200\text{ mA}; \text{note 1}$	–	–	–300	mV
$R_{CEsat}$	equivalent on-resistance	$I_C = -2\text{ A}; I_B = -200\text{ mA}; \text{note 1}$	–	120	<150	$\text{m}\Omega$
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -2\text{ A}; I_B = -200\text{ mA}; \text{note 1}$	–	–	–1.2	V
$V_{BE}$	base-emitter turn-on voltage	$V_{CE} = -2\text{ V}; I_C = -1\text{ A}; \text{note 1}$	–	–	–1.1	V
$f_T$	transition frequency	$I_C = -100\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_e = 0; f = 1\text{ MHz}$	–	–	40	pF

## Note

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

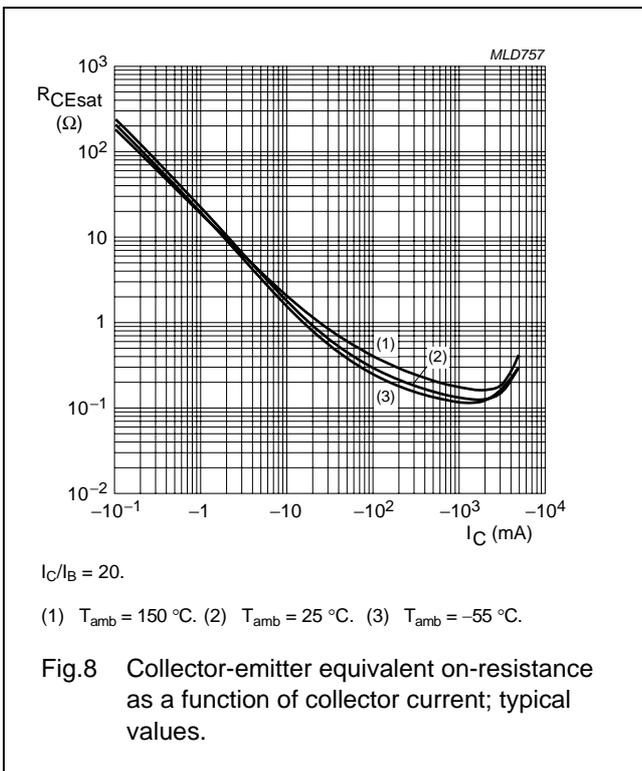
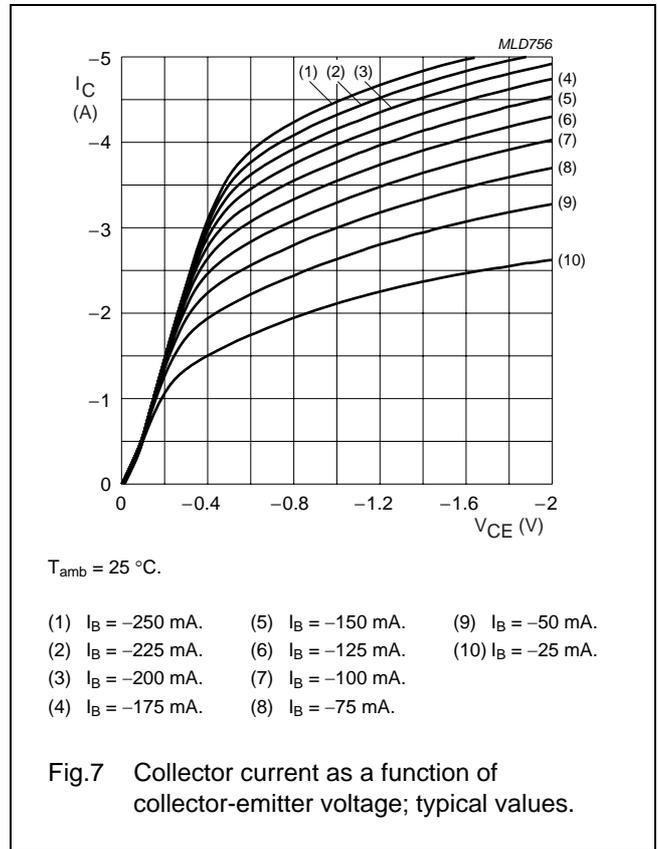
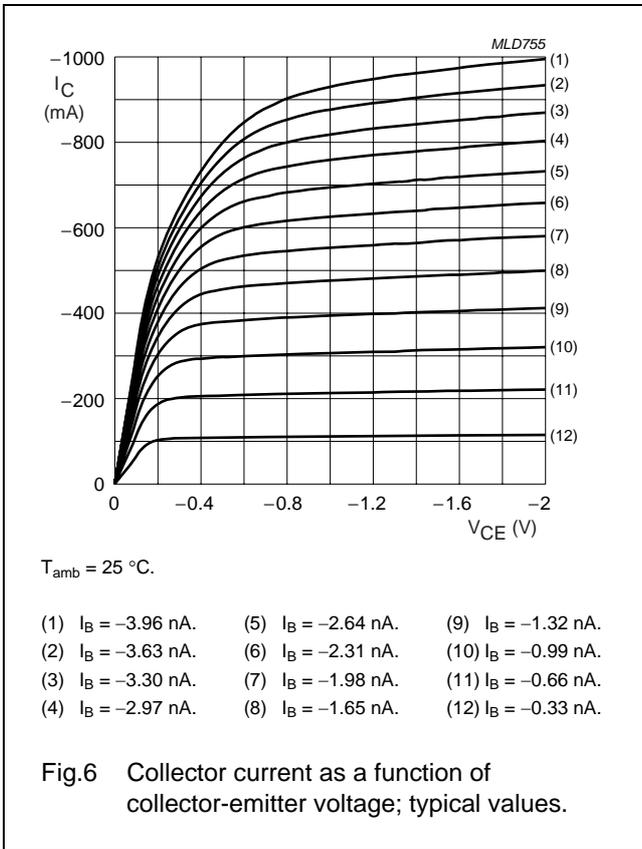
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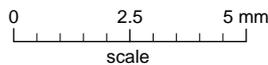
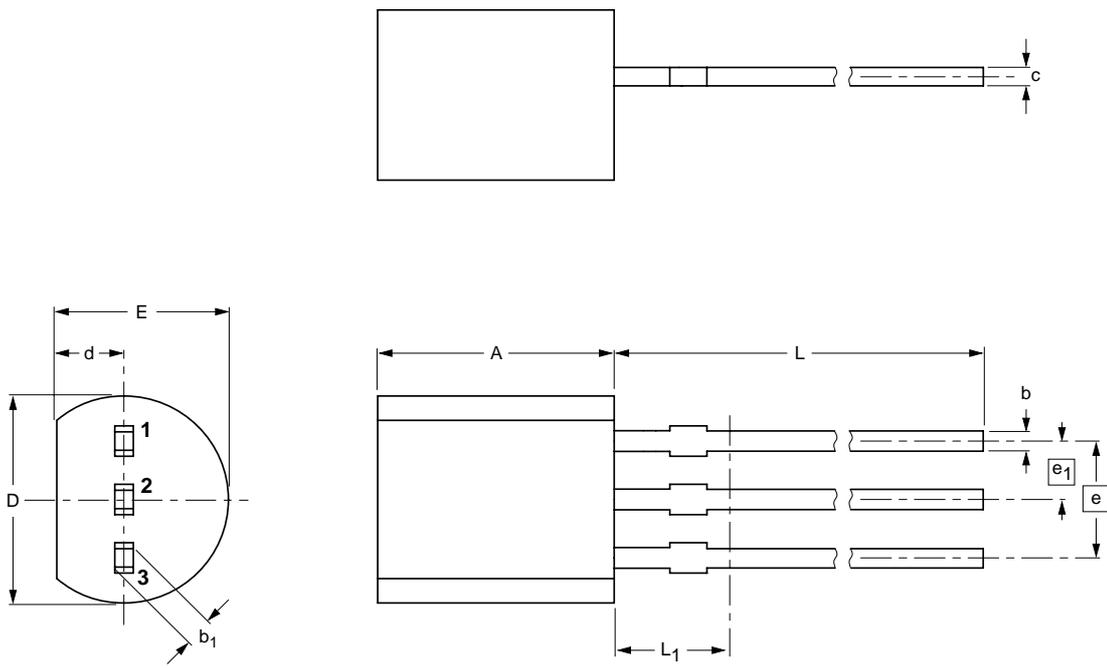
50 V low  $V_{CEsat}$  PNP transistor

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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



**DIMENSIONS (mm are the original dimensions)**

UNIT	A	b	b <sub>1</sub>	c	D	d	E	e	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup> max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

**Note**

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT54		TO-92	SC-43A		04-06-28 04-11-16

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## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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## **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

## **Contact information**

For additional information please visit: <http://www.nxp.com>

For sales offices addresses send e-mail to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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